TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U-MOS V)

TPCC8103

Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance:

 $R_{DS (ON)} = 9.4 \text{ m}\Omega \text{ (typ.)} (V_{GS} = -10 \text{ V})$

- Low leakage current: I_{DSS} = -10 μA (max) (V_{DS} = -30 V)
- Enhancement mode: V_{th} = -0.8 to -2.0 V (V_{DS} = -10 V, I_D = -1.0 mA)

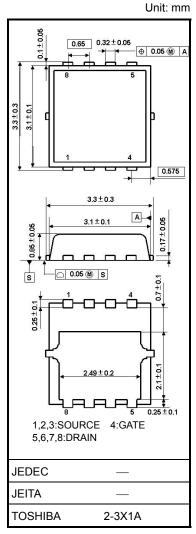
Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-30	V
Drain-gate voltage (R	$k_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	-30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I _D	-18	А
Diam current	Pulsed (Note 1)	I_{DP}	-54	ζ
Drain power dissipati	on (Tc = 25°C)	P_{D}	27	W
Drain power dissipati	on (t = 10 s) (Note 2a)	P_{D}	1.9	W
Drain power dissipati	on (t = 10 s) (Note 2b)	P_{D}	0.7	W
Single-pulse avalance	ne energy (Note 3)	E _{AS}	84	mJ
Avalanche current		I _{AR}	-18	Α
Repetitive avalanche (To	energy = 25°C) (Note 4)	EAR	1.59	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature	range	T _{stg}	-55 to 150	°C

Note: For Notes 1 to 4, refer to the next page.

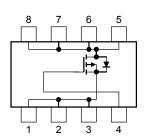
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.02 g (typ.)

Circuit Configuration

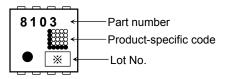


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Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R _{th (ch-c)}	4.7	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	66	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	180	°C/W

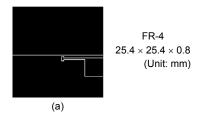
Marking (Note 5)

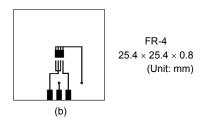


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: $V_{DD} = -24~V$, $T_{ch} = 25^{\circ}C$ (initial), $L = 200~\mu H$, $R_G = 25~\Omega$, $I_{AR} = -18~A$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



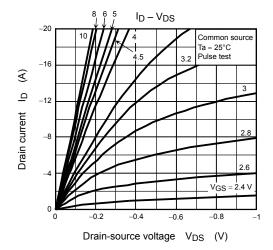


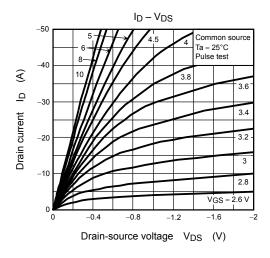
Electrical Characteristics (Ta = 25°C)

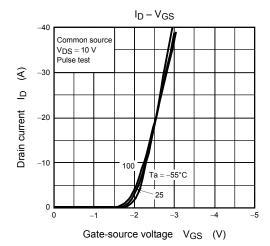
Ch	naracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cui	rrent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$		_	-10	μА
Drain agurag bro	akdowa voltago	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	_	_	V
Diain-source bre	akdown voitage	V _{(BR) DSX}	$I_D = -10 \text{ mA}, V_{GS} = -20 \text{ V}$	- ±100 10 -30	v		
Gate threshold v	oltage	V _{th}	$V_{DS} = -10 \text{ V}, I_D = -1.0 \text{ mA}$	-0.8	_	-2.0	V
Drain aguras ON	ragintance	R _{DS} (ON)	$V_{GS} = -4 \text{ V}, I_D = -9 \text{ A}$	_	17	25	- mΩ
Drain-source ON	-resistance		V _{GS} = -10 V, I _D = -9 A	_	9.4	12	
Forward transfer admittance		Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -9 \text{ A}$	15	30	_	S
Input capacitance	e	C _{iss}		_	1600	_	
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	340	_	pF
Output capacitance		Coss			490	_	
	Rise time	t _r	VGS 0 V]	_	9.3	_	
	_]					
	Fall time	t _f	700 ~ -15 V	_	68	_	ns
	Turn-off time			_	175	_	
	' Q ₀ -		_	38	_		
Gate-source charge 1		Q _{gs1}	I _D = -18 A	_	4.5	_	nC
,		Q _{gd}		_	11	_	

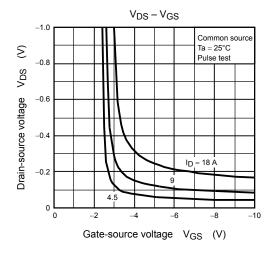
Source-Drain Ratings and Characteristics (Ta = 25°C)

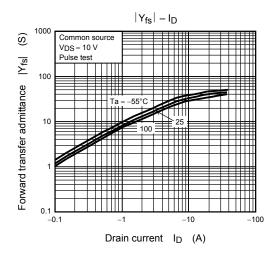
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	_	_	_	-54	Α
Forward voltage (diode)			V_{DSF}	$I_{DR} = -18 \text{ A}, V_{GS} = 0 \text{ V}$	_		1.2	V

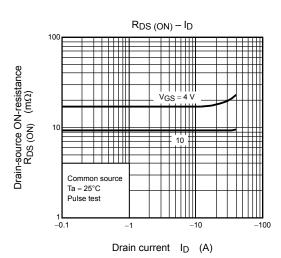




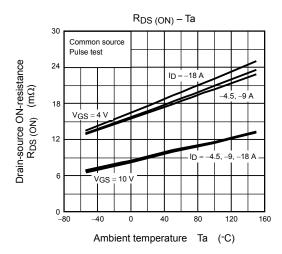


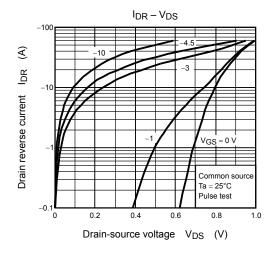


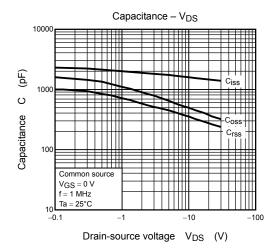


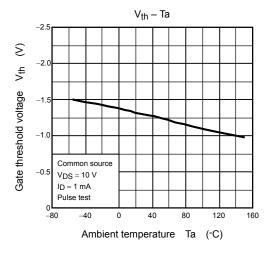


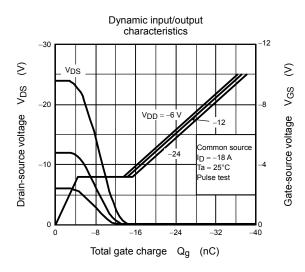
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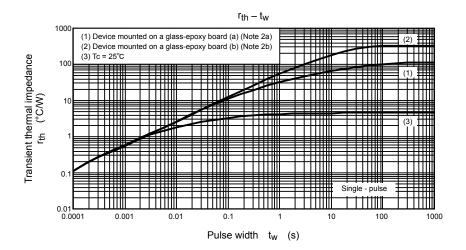


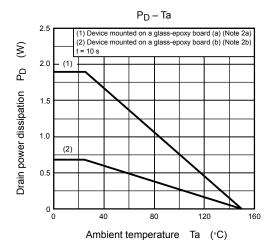


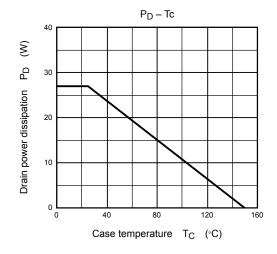


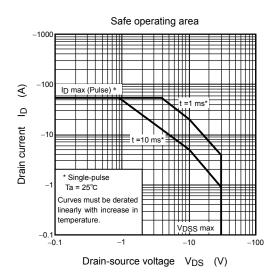


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